

2N3866 2N3866A

JAN, JTX, JTXV AVAILABLE
CASE 79-02, STYLE 1
TO-39 (TO-205AD)

HIGH FREQUENCY TRANSISTOR

NPN SILICON



MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	30	Vdc
Collector-Base Voltage	V_{CBO}	55	Vdc
Emitter-Base Voltage	V_{EBO}	3.5	Vdc
Collector Current — Continuous	I_C	0.4	Adc
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	5.0 28.6	Watts mW/°C
Storage Temperature	T_{stg}	-65 to +200	°C

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
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OFF CHARACTERISTICS

Collector-Emitter Breakdown Voltage ($I_C = 5.0 \text{ mAdc}$, $R_{BE} = 10 \Omega$)	$V_{CER(sus)}$	55	—	Vdc
Collector-Emitter Sustaining Voltage ($I_C = 5.0 \text{ mAdc}$, $I_B = 0$)	$V_{CEO(sus)}$	30	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 100 \mu\text{Adc}$, $I_C = 0$)	$V_{(BR)EBO}$	3.5	—	Vdc
Collector Cutoff Current ($V_{CE} = 28 \text{ Vdc}$, $I_B = 0$)	I_{CEO}	—	0.02	mAdc
Collector Cutoff Current ($V_{CE} = 30 \text{ Vdc}$, $V_{BE} = -1.5 \text{ Vdc (Rev.)}$, $T_C = 200^\circ\text{C}$) ($V_{CE} = 55 \text{ Vdc}$, $V_{BE} = -1.5 \text{ Vdc (Rev.)}$)	I_{CEX}	— —	5.0 0.1	mAdc
Emitter Cutoff Current ($V_{BE} = 3.5 \text{ Vdc}$, $I_C = 0$)	I_{EBO}	—	0.1	mAdc

ON CHARACTERISTICS

DC Current Gain ($I_C = 360 \text{ mAdc}$, $V_{CE} = 5.0 \text{ Vdc}$) ($I_C = 50 \text{ mAdc}$, $V_{CE} = 5.0 \text{ Vdc}$)	Both 2N3866 2N3866A	h_{FE}	5.0 10 25	— 200 200	—
Collector-Emitter Saturation Voltage ($I_C = 100 \text{ mAdc}$, $I_B = 20 \text{ mAdc}$)		$V_{CE(sat)}$	—	1.0	Vdc

SMALL SIGNAL CHARACTERISTICS

Current-Gain — Bandwidth Product ($I_C = 50 \text{ mAdc}$, $V_{CE} = 15 \text{ Vdc}$, $f = 200 \text{ MHz}$)	2N3866 2N3866A	f_T	500 800	— —	MHz
Output Capacitance ($V_{CB} = 28 \text{ Vdc}$, $I_E = 0$, $f = 1.0 \text{ MHz}$)		C_{obo}	—	3.0	pF

FUNCTIONAL TEST (FIGURE 1)

Amplifier Power Gain ($V_{CC} = 28 \text{ Vdc}$, $P_{out} = 1.0 \text{ W}$, $f = 400 \text{ MHz}$)		G_{pe}	10	—	dB
Collector Efficiency ($V_{CC} = 28 \text{ Vdc}$, $P_{out} = 1.0 \text{ W}$, $f = 400 \text{ MHz}$)		η	45	—	%

FIGURE 1 - 400 MHz TEST CIRCUIT SCHEMATIC

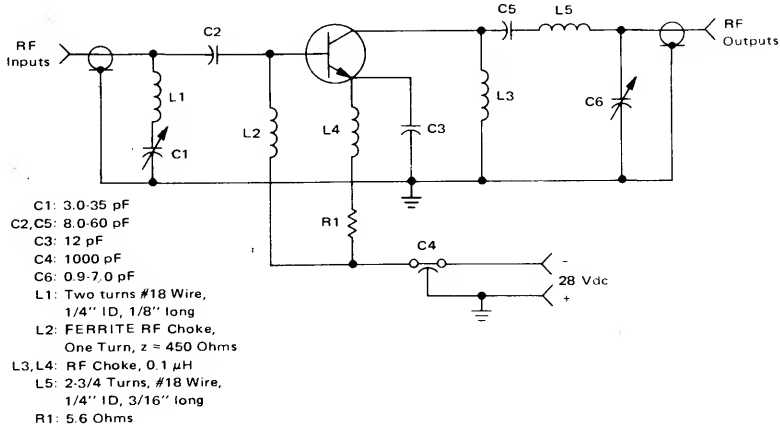


FIGURE 2 - POWER OUTPUT versus FREQUENCY (Class C)

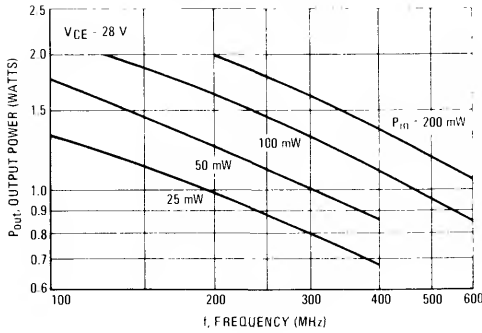


FIGURE 3 - CURRENT GAIN - BANDWIDTH PRODUCT

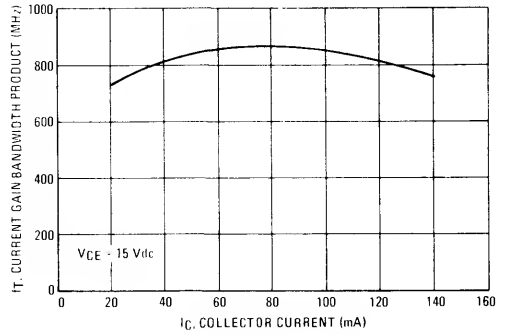


FIGURE 4 - COLLECTOR-BASE TIME CONSTANT

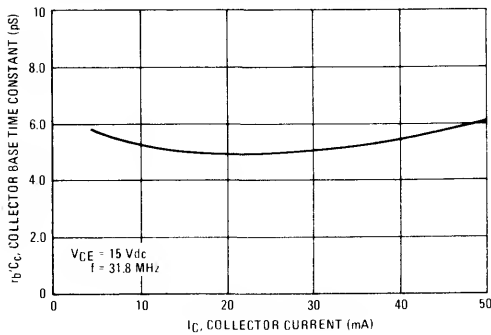


FIGURE 5 - OUTPUT CAPACITANCE

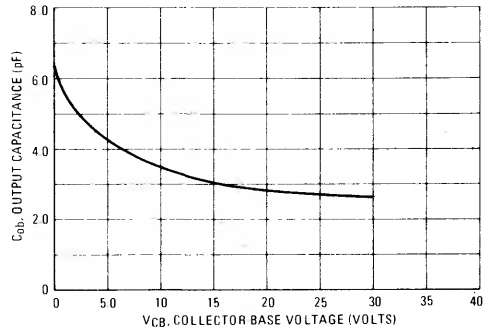


FIGURE 6 – OUTPUT POWER versus INPUT POWER (CLASS C)

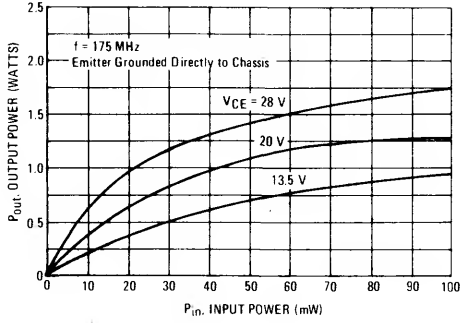


FIGURE 7 – SMALL SIGNAL CURRENT GAIN

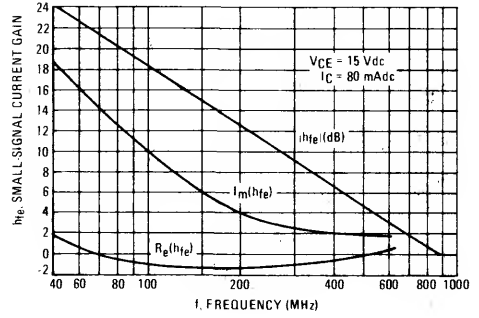


FIGURE 8 – LARGE-SIGNAL SERIES EQUIVALENT IMPEDANCES

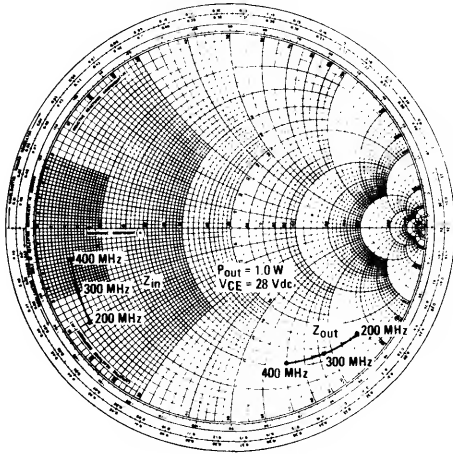
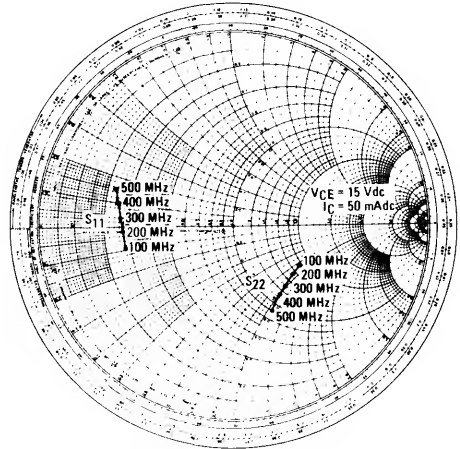


FIGURE 9 – S_{11} AND S_{22} versus FREQUENCY



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FIGURE 10 – S_{21} versus FREQUENCY

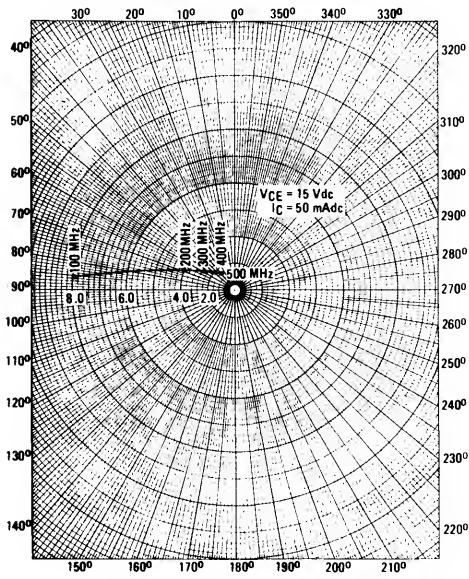
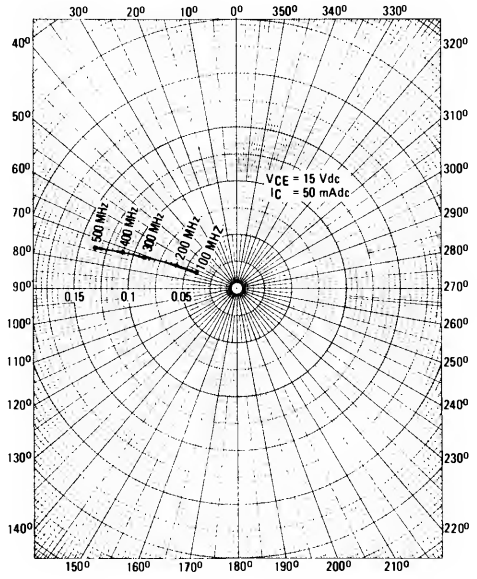


FIGURE 11 – S_{12} versus FREQUENCY



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